

SUBJECT INDEX

KEY

page number font	boldface	main subject treatment
	<i>italic</i>	figure
suffixes	ff	“and pages following”
	n	footnote
	g	graph
	r	review section
	p	photograph
	s	screen shot (‘scope or spectrum analyzer)
	t	table
	T	tabular
	boldfaceff	main entry, folios following
	(box)	in a box

absolute-value circuit, 272r

ac powered

efficient dc power supply,
415, **415**

ACRF, 14t

active

rectifier, 273r

admittance, 3

amplifier

class-AB, 425

CMOS, **217ff**, 218

bandwidth, 218g

gain, 217g

common-base, 138

cascode as, 206, 206, 207

common-emitter, 100r, 110

degenerated, 115

distortion, 113–115g,
121g

frequency response, 111,
112

linearity, 113–115g, 121g

common-gate

cascode as, 206, 206, 207

composite, 291

Bode plot, 300

stability, 299, **299ff**, 300s

current-feedback, 378

difference

amplifier difference (cont.)

vacuum tube, 276p

differential, 100r, **114**, 115

and cascode, 108, 109

Caprio’s quad, 119, 119g,
119, 121g

degenerated, 116, **116**

distortion, **114ff**, 115,

116g, 116s, 117g, 121g

emitter-input, **133ff**, 135

linearity, 115g, 121g

low-noise, 178, 179

Sziklai-connected, **116**,
117, 117g, 118, 118g,
121g

transfer function, 116g,
116s, 117g

distortion

SPICE simulation, **110ff**

error, 393r

grounded-emitter, 110

high-voltage, 185, 201, 374,
375s

bipolarity current monitor,
425, 425

Bode plot, 370g, 378g

current monitor, 424, 424

faster, **376ff**

MOSFET choices, 377t

amplifier, high-voltage (cont.)

precision, **368ff**, 369,
376ff

slew rate, 374

SPICE, 373, 373

stability, 377

variations, 375, 376

JFET

differential, 178, 179

low-noise, 178, 179

laboratory, **152ff**

lock-in, 14n

logarithmic, 362, 362

temperature compensa-
tion, 362, 362g

low-noise, 178, 179

MOSFET power, 159r

photodiode, **285**, 286, **288ff**,
289, 296, **296**, 297, 297

precision, 185

stability

decoupling resistor, 373

summing, **357**, 358, 359

transconductance, 305

transimpedance, 283, **283ff**,
296, **296**, 297, **297**, 305

amplitude

rms, 2r

- analog
 adder–subtractor, **357**, **359**
 computer, **357**, **358**, **358s**
 function circuits, **357**, **358**,
358s
- analog switch, **76**
 in TIA, **289**, **290**
- aspirin
 of electronics, **108**, **109**
- avalanche
 energy, **239**
 in diodes, **4r**
 photodiode, **348**, **348**, **349**
 voltage, **197**
- Ayrton–Perry, **21**
- B-H curve, **51s**
 and core loss, **51**
 square-loop, **51s**
 transformer, **51s**
- balanced
 drive, **433**
- bandwidth
 narrowing
 lock-in detection, **14**
 of cascode, **206ff**
 of source follower, **208**, **209**,
209ff, **210g**, **211**, **211g**
- bang–bang control, **394r**
- Barkhausen noise, **50n**
- barometric pressure
 sensor, **470**
 units, **470n**
- basket weave, **60**
- battery
 Li-ion
 cautions, **397**
 charging, **397**, **398**
 series connection, **399**,
399
 reverse polarity protection,
396, **396**
- bias tee, **61**, **63**, **63g**, **64p**
- Billings, K., **58**
- BJT (bipolar junction transistor)
 amplifier distortion, **110ff**
 as zener, **82**, **83g**, **194n**
 bandwidth, **140ff**
 beta, **137g**, **256g**
- BJT (cont.)
 capacitance, **101r**, **141**, **141g**,
144t, **207n**
 cascode, *see* cascode
 collector output resistance,
122, **122**, **123g**, **124ff**
 collector-base time constant,
144, **145g**
 current source, **99r**
 canceling base-current er-
 ror, **356**, **356**
- Darlington, **101r**
 transconductance, **255g**
 transfer characteristics,
254, **255g**
- Ebers–Moll model, **98r**
- emitter resistance
 intrinsic, **99r**
- gain-bandwidth product,
140ff, **144t**
 vs current, **142**, **143g**
- hybrid- π model, **140**
- leakage current, **102g**, **102**
- maximum oscillation fre-
 quency, **144**
- maximum voltage gain, **124**
- micropower wideband, **144**
- MOSFET substitute, **135**
- operating modes, **97r**
- pin labels, **97r**
- polarities, **97r**
- power, **254**, **254T**
- rules of thumb, **98r**
- switch, **97**, **98r**
- Sziklai connection, **101r**,
126ff, **127**, **127g**, **256**
 differential amplifier, **116**,
117, **117**, **117g**, **118**,
118, **118g**, **121g**
 enhanced, **126**
 push-pull follower, **128**,
128
- transconductance, **97**, **98r**,
255g
- transfer characteristics, **254**,
255g
- Bode plot, **278**, **278ff**, **299**, **365**,
370g, **371**, **372g**, **378g**
- composite amplifier, **300**
- in amplifier design, **280**
- of TIA, **284**
- bootstrap
 cascode, in TIA, **297**, **297**
 leakage cancelation, diode,
355
 of bias resistor, **214**, **215**,
215s
 of power supply, **416**
 of TIA, **296**, **296**, **297**, **297**
- bridge
 converter, **393r**
 rectifier, **392r**
- Brooks coil, **49**
- buffer
 unity-gain, **299ff**, **303T**
 applications, **300**
 cautions, **302**
 input resistor, **302g**
 output resistor, **302g**
 peaking, **302g**
- bus
 converter, **442**, **442**, **443**,
444, **445p**
 isolated, **445**, **445**
- cable, *see also* transmission line
 cat-5, **9**, **13**, **13p**, **14t**, **15p**
 cat-6, **9**
 coax, **9**
 configurations, **9ff**
 driving, **299**
 FFC, **15p**
 Milliken, **11p**, **12**, **12**
 multiwire, **9**
 ribbon, **10**, **15p**
 shielded, **9**
 STP, **15p**
 twisted-pair, **13**
 inductance of, **10**
- camera
 FLIR, **466ff**, **466–468p**
 thermal, **466ff**, **466–468p**
- capacitance
 as villain, **288**
 dynamic, **84n**
 junction, **101r**
 multiplier, **94**, **94**, **416**, **451**,
451, **452**, **452s**
 of diode, **80**, **81**, **81**, **82g**, **83**,
478
 of resistor, **20**, **20**, **21g**

- capacitance (cont.)
 of zener, 81, 82g, 83, 478
 PCB, 7, 8g
- capacitive
 isolator, 248
- capacitor, 2r, **34ff**
 ac line filter, 44
 ac powerline rated, 428
 ac voltage coefficient, 40g, **40**
 aging, **40**
 blocking, 3r
 bypass, 3r, 42
 ceramic, 34t, 35g, 36t
 aging, 40g
 micro-cracks, 44n
 voltage coefficient, 38g
- choices, **42**
- compensation, 247, 393r
 tunable, 296
- decoupling, 42
- departure from ideal, 34ff
- dielectric absorption, 42g, **42**, 43, 43g, 269
- dissipation factor, 36, 37, **37**, 38t
- electrolytic
 derating, 44
 energy storage, 44
 ESL, 34, **36**, 37g, 480
 ESR, 34, **35**, 480
 vs size, 36, 36g
 vs temperature, 36g
- exploding, 43n
- family tree, 35
- frequency dependence, **40**, 41g
- gimmick, 44, 45n
- high frequency, 43
- high voltage, 44
- impedance
 vs frequency, 37g
- loss tangent, **37**
- mechanical resonance, **40**, 41g, 41, 42s
- microphonic, **40**, 41, 42s
- miscellany, 44
- model, 34
- non-ideal, 34ff
- nonlinearity, 39g
- capacitor (cont.)
 piezoelectric, 41g
 selecting, **42**
 solid polymer, 36
 storage, 3r, 244, 392r
 sub-picofarad, 287, 287, 288
 tempco, **34**, 34t, 35g, 36t, 38g
 timing, 3r, 43
 types, 35, 44
 ultra, 45
 voltage coefficient, 38g, **38**, 39, 39g
- capacity
 thermal, 482
- Caprio's quad, 119, 119g, **119**, 121g
 with folded cascode, 119, 120, 120, 120, 121g
- cascode, **108ff**, 109, 150, 173, 174, 175, 176, 177t, 178, 179, 179, 193, 194g, 196, 196, 196g, 197, 197, 198g, 267, 332, 333, 333
 and differential amplifier, 108, 109
 and Early effect, 108, 109
 and high voltage, 108
 and Miller effect, 108, 109
 and transimpedance amplifier, 108, 109
 as common-gate amplifier, 206, 206, 207
 bandwidth, **206ff**, 207
 folded, 119, 120, 120, 120, 121g, 129, 130, 150
 in current mirror, 103, 104
 in current source, 194, 195
 in differential amplifier, **118**
 series stack, 216
- CERN, 22
- charge
 dispenser, **266ff**
 MOSFET gate, 159r
 pump, 245, 246, 253, 267n, 392r, 439
 Marx generator, 439
- choke, **59ff**, 61, 62g, 62p, 63g
 bank-winding, 62
 common-mode, 433
- circuit
 breaker, 477, 478
- clamp
 anti-soar, 456
 low-capacitance, 476, 478
 low-voltage, **412**, 413
- CMOS
 linear amplifier, **217ff**, 218
 bandwidth, 218g
 gain, 217g
- Cockcroft–Walton generator, 439
- coil
 Helmholtz, 14, 16p
- cold-junction compensation, 471
- comparator, 100r, 273r, 393r, 423
- compensation, **278ff**
 cold-junction, 471
 pole-zero, 456
- conduction
 angle, 253
 class-A, 233
- confidence
 misplaced, 456
- connector, **15ff**, 19p
 0.9mm, 18t
 1.85mm, 18t
 2.4mm, 18t
 2.92mm, 18t
 APC-7, 18t
 audio, 17
 avoid these, 17
 BNC, 17, 18g, 18t
 D-sub, 17, 18, 19p
 DIN, 17
 F, 17
 FFC, 19p
 header, 19p
 high-density, **18**
 high-voltage, 17
 K, 61
 MCX, 18t
 MMCX, 18t
 power-entry, 17
 RCA, 17
 rectangular, 17
 reflection from, 17, 18g
 RF and shielded, 17, **17ff**, 18g, 18t
 RM, 17
 SC, 18g

- connector (cont.)
 SHV, 17
 SMA, 17, 18g, 18t, 61
 SMB, 17, 18t
 SMC, 18t
 3.5mm, 18, 18t
 SSMA, 18g, 18t
 superSMA, 18t
 TNC, 18g, 18t
 type N, 18g, 18t
 UHF, 17, 18, 18g, 18t
 V, 61
 XLR, 17
- contactor, 265
- control
 bang–bang, 394r
- coplanar waveguide, 8
- coupling
 electrostatic, 12
 magnetic, 12
 mitigation, 13
 test circuit, 13, 13s
 unwanted, **12ff**
 mitigation, 13
- creepage, 428
- cricket
 as thermometer, 465
- crosstalk, 12, 13, 13s, 14t
- crowbar, 353
 overvoltage, 393r, 395r
 low-voltage, **412**, 413
- current, 2r
 bound, 46n, 50
 conduction, 46n, 50
 dynamic, 382
 eddy, 10, 14
 free, 50
 harmonic, 418n
 high-side sensing, **423ff**
 ICs, 427T
 in wires, 5
 inrush, 418, 418–420s
 junction leakage, 4r
 leakage, 77, 77g
 actual, **102**
 diode, 4r
 diode, eliminating, 364, 364
 vs temperature, 77, 78g
 vs voltage, 78g
- current (cont.)
 limiting, 393r, 423
 foldback, 146, 146, 146, 147g
 recombination, 136g
 saturation, 181
 sensing
 ICs, 427T
 shoot-through, 244, 246, 248, 256
 tunnel, 90
- current mirror, 99r, **105**, 380
 bipolarity, 129, **129ff**, 130s
 high ratio, 133, **133**, 134
 monolithic, 105
 multiple output, 105, 105
 piezo driver, 269, 269
 ratio, 105, 106, 106g
 Widlar, 105, 106, 106g
 Wilson, 106
 monolithic, 105
 wilson, 103
- current source, **103ff**, 104, 354, 395r
 V_{BS}-referenced, 105
 2-terminal, 381
 bipolarity, 129, **129ff**, 130, 130s, 380, **380ff**, 381
 high voltage, 130, 131
 precision, **131**, 132
 canceling base-current error, 356, 356
 cascode in, 103, 104
 deficiencies of, **103ff**
 depletion-mode, 193, **193ff**, 194, 194g
 dissipation, 381
 errors, 382
 fast-switching, 479, 480
 floating, **193ff**
 gain, 388
 high-voltage, 197, **197ff**, 198, 199g, 201–203g, 204, 380, **380ff**, 381, 389, 425
 “perfect”, 204
 LM334, 107
 magnet
 fast-switching, 479, 480
 MOSFET, 266
- current source (cont.)
 output resistance, 104, **125**, 194g
 dynamic, 194, 195
 programmable, 107
 programmed cascode, 196, 196
 reducing power dissipation, 195, 195, 196, 196g, 197, 198g
 slew rate of, 382
 tempco, 103, 104
- current-crowding, 136
- damping
 ratio, 284
- dB, 2r
- dc
 motor model, 407, **407**
- decapot, *see* resistor, digital
- delta function, 87
- Designs by the masters
 bulletproof input protection, **353ff**, 354
 PG508 pulse generator, **150ff**, 151, 152, 153s
- dielectric
 absorption, 42g, **42**, 43, 43g
 constant, 38, 40, 40n
- digipot
 frequency response, 31g
 log approximation, 31g
- diode, 4r, **77ff**
 back, 92
 capacitance, 80, 81, 81, 82g, 83, 478
 characteristics, 77
 fast recovery, 264
 fast-recovery, 85
 FERD, 85
 forward current, 77, 78, 79g
 forward drop
 tempco, 79g
 forward dynamic impedance, 79, 79g
 forward recovery, 88, 89s
 freewheel, 264
 input protection, 81, 478
 leakage, 77, 77, 78g
 eliminating, 364, 364

- diode (cont.)
 peak current, 80, 81g
 reverse recovery, **83ff**, 84s, 85g, 85s, 86g, 410, *410*, 411s, 430, 456
 test circuit, 83, 83
 Schottky, 79g, 85, 410
 soft-recovery, 85
 step-recovery, **86**, 87s, 88, 89s
 test circuit, 86
 stored charge, **83ff**, 84s, 85, 86g, 410, *410*, 411s, 430, 456
 test circuit, 83, 83
 transient thermal resistance, 81g
 tunnel, **89**, 90
 VI curve, 90, 90, 91, 92s
 test circuit, 91, 91, 92p
 trigger, 92, 92, 92s
 zener, 394, *478*
 VI plot, 80g
 2-stage protection, 82, 83
 bidirectional, 474, 475
 BJT as, 82, 83g
 capacitance, 81, *478*
 input protection, 81, 476, *478*
 TVS, **476**, *478*
 zero-voltage dynamic impedance, 80, 80g
- discharge
 of high-voltage supply, 427, 427, 427s
- distortion
 crossover, 378
 in BJT amplifiers, **110ff**
- DMM, 353, *354*
- duolateral, 60
- Early effect, 98r, 103, 122g, **122ff**, 123g, 174, 175, 184
 and cascode, 108, *109*
 configurations that avoid, 98r
 feedback factor, 123
 formulas, 123
 measuring, 122
 MOSFET analog, 196
- EEpot, 28, 29, 30t
 parameters, **28**
- electro-optic shutter, 250
- electromagnetic
 conversion factors, 46t
- electromagnetic interference (EMI), 308
- EMF
 back, 46, 406
- emitter
 degeneration, 98–100r
- emitter follower, 99r
 inductive output, **148**, 148s, *149*
 oscillations in, *138*, **138ff**, 138s
 output impedance, **148**, 148s, *149*
- EnergyStar, 415, 417
- Esaki, L., 89n
- eye diagram, 327s
- fan
 brushless, 456, 457s
 ceiling, 438
 ramp-up, 405s
- Faraday cage, 13
- Faraday's law, 46
- feedback, 101r
 PID, 471
 motor control, 406
 stability, 278, **278ff**
- ferrite
 bead, 138, *138*, 456
 cores, 436p
- ferromagnetic, 50
- FET
 avalanche, 185, 185g
 drain characteristics, 180, 180, 181g
 enhancement and depletion, 157r
 gate current, 158r
 linear region, 158r
 operating regions, 157r
 output resistance variation, 184g
 polarities, 157r
 resistive region, 180
 saturation region, 157r, 180
 subthreshold region, 158r, 181g, **182ff**, 183g
- FET (cont.)
 switch, 158r
 threshold voltage (V_{th}), 181g, 183g, 186g
 threshold voltage (V_{th}), 183
 transconductance (g_m), 157r
 transfer characteristics, 181g, 183g
 triode region, 180, 181
- filter
 active
 lowpass, 290, 290g
 bandpass, 435
 Butterworth
 poles of, 67
 power-supply, 392r
 RC highpass, 3r
 RC lowpass, 3r
- frequency
 comb, 87, 88s
 complex, 65
- fretting, 19
- fuse, 392r
 thermal, 477
- Garwin, R. L., 14n
- gas discharge tube, 353
- GDT, 474, *475*, **475**, *475p*, *478*
- gimmick, 44
- Graham, M., 10n
- Grover, F.W., 10n
- Gummel plot, 98r, 136, 137g
- H-bridge, 471
- half bridge, 266
- Hanna curve, 56
- harmonic
 comb, 88s
- harmonic current, 418
- heat, 394r
- heatsink, 395r
- Helmholtz coil, 14, 16p, 264
- high-voltage
 amplifier, 185, 374, 375s
 Bode plot, 378g
 precision, **368ff**, 369, **376ff**
 stability, 377
 circuits and cascode, 108
 current source, **380**, **381ff**
 2-terminal, 381

- high-voltage (cont.)
 monitor, 247, 249
 pulse generator, 244, 246
 bipolarity, 249, 250
 reversible, 247
 ramp, 262, 263
- honeycomb, 60
- hysteresis
 magnetic, 50, 51s
- IGBT, 264, 265, 265p
- IGBT (insulated-gate bipolar transistor), 160r, 252
 fault protection, 252
 linear applications, 254, 254T
 transconductance, 255g
 transfer characteristics, 254, 255g
 vs BJT, 254
 vs MOSFET, 252t, 481
- impedance, 2r
 loading effect of, 3r
 negative, 406
 of PCB transmission line, 7
- inductance, **10ff**
 formulas, 10
 leakage, 411t
 spike, 410, 410, 411s, 430, 456
 mutual, 47
 of resistor, 20, **20**, 21, 22g
 of wire, 10, 10g
 PCB, 7, 8g
 scaling, 47
 self, 47
- inductive
 transient
 TVS suppressor, 479, 480
- inductor, 2r, **46ff**, 436p
 N-turn loop, 49
 air core, **46**
 coefficient, 48g
 copper loss, 54
 core
 thermal resistance, 55g
 core loss, 51, 54, 54g, 406
 core materials, 49
 core size
 nomogram, 59
- inductor (cont.)
 examples, **59**
 for switching converters, 60
 gapped core, 55, **55**, 56, 57g, 57t
 lossy, 58, 58s
 magnetic-core, 49
 RF choke, **59ff**, 61, 62g, 62p, 63g
 saturation, 53, 133, 133g, **133**, 134
 shortcuts, **53**
 solenoid, 47
 air-core, 47
 ferrite core, 52g, **52**, 52p, 53g
 inductance of, 47
 square-loop, 58, 58s
 stored energy, 393r
 TVS suppressor, 479, 480
 tapered, 63p
 toroid, 49, **49**
 ferrite core, **52**
 transient isolator, 248
 tunable, 57
 types, 47p
 Wheeler's formula, 48
- inductors
 for power converters, 58
- input
 protection, 213, 215, 215s, 291, **353ff**, 354
- instrumentation amplifier, 272r
 autozero, 423
- integrator
 reset, 272r, 291
 windup, 378
- JFET (junction field-effect transistor), **161ff**, 162t
 G_{\max} , **175ff**, 178, 178
 R_{ON} , 164
 V_{GS} spread, 163, 164g
- amplifier
 biasing, 158r
 common-source, **175ff**, 176, 177t, 207
 low-noise, 178, 179
 vs switch, 164
- bandwidth, 207t
- JFET (cont.)
 capacitance, 165, 167t, 207t
 cascode, 173, 174, 175, 176, 177t
 dual, 165
 families, 161
 gain
 maximum, **175ff**, 176g, 177t
 gate current, 102g, **102**, **166**, 167g, 167t, 293
 gate leakage, 294
 impact-ionization current, 166, 167g
 proportional to drain current, 166, 167g
 manufacturing spread, 295
 output resistance, 175g, **175ff**, 176, 176g, 177, 177t, 178, 178, 178g
 packages, 161, 161
 parameter interaction, 164g
 pinch-off voltage, V_p , 163
 source degeneration, 176, 176
 source follower, 172
 switch, 158r
 vs amplifier, 164
 transconductance, **169ff**, 176, 207t
 enhancer, 171, 171t, 172, 178, 179
 equations, 169
 maximum gain, 165
 measuring, 174, **174**
 of source follower, 172, 173
 vs BJT, 169, 169
 vs drain current, **169**, 170, 171g
 vs drain voltage, **170**, 171g
 within a family, 164, 165g
 transfer characteristics, 163, 164g
- Johnson noise, 456
- Johnson, H., 10n
- Kelvin connection, 134
- Kelvin, Lord, 48n
- kickstart, 416

- Kirchhoff's laws, 2r, 387
 nodal analysis, **386ff**, 387
- Kirchhoff, G., 48n
- Larkin, John, 24
- laser diode, 461, 462g, 462p
- lattice-wound, 60
- LC
 series, 436
- LC
 resonant circuit, 3r
 series, 435
- leading-edge detector, 94, 94
- LED
 VI plot, 80g
 chip-on-board (COB), 463, 463p, 464g, 464p
 forward drop, 79g
 pulser, 258, **258ff**, 259, 260
- level shifter, 370
- linear
 circuit, 2r
- litz wire, *see also* wire, *see* wire, 12
- LNB, 61
- load
 capacitive, 371, 372, 372, 372g
 op-amp, **365ff**, 366g, 366s
- loading, 3r
- logic
 CMOS, 159r
 linear amplifier, 217g, **217ff**, 218, 218g
 oscillator, 218
 transfer characteristics, 217g
 unbuffered, 217, 217g
 isolator, 248
 parasitic coupling, 13s
 timing skew, 9, 9
 wired-OR, 423
- Lorenz attractor, **357**, 358, 358s
- Lorenz, L., 48n
- loss
 switching, 406, 416
- Lumen, 459
- luminous efficiency, 460g, 460T
- magnet
 fast shutoff, 264, 265, 265p
 fast-switching, 479, 480
 transient suppression, 479, 480
- magnetic
 core
 gapped, 55, **55**, 56, 57g, 57t
 thermal resistance, 55g
 wire capacity, 55g
 core loss, 51, 54, 54g, 406
 domain, 50, 51
 hysteresis, 50, 51s
- Mandelbrot set, 357
- Marx generator, 439, 440
- Maxwell's equations, 49, 52n
- Maxwell, J.C., 48n, 49
- microstrip, 8
 impedance, 8g
- Miller effect, 101r, 129, 140, 144, 150, 151, 179, 226, 233, 235
 and cascode, 108, 109
- Milliken, H., 11n, 12
- Monticelli output circuit, 339, **339**, 340g
 SPICE simulation, **339**
- MOSFET
 R_{ON} vs temperature, 251g, **251ff**
 R_{ON} vs voltage, 220
 at high voltage, 184
 at low voltage, 183
 avalanche, 185, 185g
 avalanche rated, 185, 238, 239, 239
 bandwidth, 208
 capacitance, 188g, 208, 461
 choosing, 222
 current source, 386
 enhancement-mode, 204
 nodal analysis, **386ff**, 387
 depletion-mode, 160r, 231
 as current source, 193, **193ff**, 194, 194g, 196, 196, 196g
 extending voltage of, 197, **197ff**, 198, 199g, 201–203g
- MOSFET, depletion-mode (cont.)
 high-voltage current source, 197, **197ff**, 198, 199g, 201–203g, 204
 HV discharge, 427, 427, 427s
 programmed current source, 196, 196
 SMPS startup, 416
 transfer characteristics, 202g
 die size, 220
 drain characteristics, 180, 180, 181g, 236g
 E-HEMT, 231
 extending voltage of, 197, **197ff**, 198, 199g, 201–203g
 feedback factor, 196
 figure of merit, 221, 221t
 flying, 244, 246, 248, 423
 gallium nitride, 222, 227g, 253
 gate charge
 depends on I_{load} , 233
 depends on V_{drain} , 234
 measuring, 233
 test circuit, 234, 235
 gate driver, 242, 242, 243T, 248, 424
 explosion, 247
 half-bridge, 244, 245, 246, 250T
 high-side, 244
 high-voltage, 185, 187T, 377t
 transconductance, 187T
 history, **219ff**
 inductive load, 239
 IRF-series, **219ff**, 219t, 256
 IRFZ-series, 220, 220t
 lateral, 231, 254, 255
 tempco, 254
 transconductance, 255g
 transfer characteristics, 254, 255g
 leakage, 267n
 linear applications, **180ff**, 254, 254T
 low-voltage, 191, 192g

MOSFET (cont.)

- maximum current, 159r, 220, 220t
- maximum ratings, 159r
- output characteristics, 180, 180, 181g, 236g
- output resistance
 - variation, 184g
- paralleling, 182
- pass transistor, 455
- pentode region, 181
- pHEMT, 231
- power
 - gate charge, 159r, 233, 234s, 236g, 236s, 244
 - linear applications, 254, 254T
 - paralleling, 160r
 - silicon carbide, 423
 - switch, 159r
 - transient, 238g, **238ff**, 240g
- pulse energy, 238g, **238ff**, 240g
- resistive region, 180
- RF, 231
- $R_{DS(ON)}$, 159r
- saturation region, 180
- series string of, 197, **197ff**, 198, 199g, 201–203g, 216
- shrink, **221**
 - in linear amplifier, 222, 256
- silicon carbide, 222, 227g, 248, 248s, 253, 423, 423n
 - die size, 247g
 - gate driver, 253
- SOA, 182, 182g
- source follower, 213, 214
 - bootstrapped, 213, 215, 215s
 - capacitive load, 209, **209ff**, 210g, 211, 211g
- SPICE models, 186g, **187ff**, 189, **189ff**, 189n, 190, 191
- capacitances, 190
- circuit, 189

MOSFET (cont.)

- Spirito effect, 182, 182g
 - substitute for BJT, 135
 - subthreshold, 192g
 - subthreshold region, 181g, **182ff**, 183g, 185–187, 196
 - super-junction, 191, 222, 223, 227g
 - die size, 247g
 - switch
 - bidirectional, 249
 - threshold voltage (V_{th}), 181g, 183g, 186g
 - selectable, 191, 192g
 - threshold voltage (V_{th}), 183
 - transconductance, 186, 187T, 188g, 255g
 - vs BJT, 186, 186–188g
 - transfer characteristics, 181g, 183g, 186g, 254, 255g
 - transient thermal resistance, 238, 238g, 240g
 - triode region, 180, 181
 - turn-off delay, 245n
 - vertical, **219ff**, 221, 221
 - vs BJT, 254
 - vs IGBT, 252t, 481
 - zero-threshold, 191, 192g
- motor
- drive, 408, 408g
 - model, 407, **407**
 - op-amp analogy, 408, 408, 409
 - rheostat controller, 408, 408g
- motor driver
- PWM, **403ff**, 404, 404s
- motor-generator, 405s
- MOV
- vs TVS, 477
- Nagaoka, 48g
- NEXT, 14t
- nodal analysis, **386ff**, 387
- node
- equations, 387
- noise
- brushless fan, 456, 457s
 - canceler, 360
 - common-mode, 432, 433

noise (cont.)

- power supply, 432, **432ff**, 433s, 435s, 435T, 436s, 457s
 - suppression, 58, 58s
 - Norton equivalent circuit, 3r
- op-amp
- active clamp, 273r
 - active rectifier, 273r
 - bandwidth, 274r, 306, 306g
 - basic circuits, 272r
 - bias canceled, 307g, **332ff**, 333, 334
 - current noise, 335
 - BJT, 274
 - input current, 274
 - Bode plot, 274r
 - capacitive load, 300, 351, **365ff**, 366g, 366s
 - frequency of oscillation, 365
 - cautions, 273r
 - charge dispenser, 268, 269
 - CMOS, 274r
 - input current, 274r
 - common-mode input range, 274r
 - compensation, 274r
 - current feedback, 304, 304, 305, **316ff**, 317, 320, 322T, 352
 - applications, 320
 - bandwidth, 316, 318g, 321
 - cautions, 318
 - input capacitance, 319g
 - input current, 317
 - modeling, 320
 - output current, 316
 - output swing, 323
 - precision, 317
 - slew rate, 316, 330
 - stability, 316, 318, 319g, 319s, 319t
 - current source, 386
 - MOSFET, 386
 - decompensated, 291
 - departure from ideal, 273r
 - difference amplifier, 272r
 - differentiator, 272r

- op-amp (cont.)
- discrete, 277, 277p
 - distortion, 308
 - electrometer, 274r
 - follower, 272r
 - full-power bandwidth, 306
 - gain, 274r
 - gain–bandwidth product, 306
 - vs quiescent current, 308, 309g
 - golden rules, 272r
 - high-speed, 281, **304ff**, 312–315T, **316ff**, 322T
 - history, **276ff**
 - ideal, 272r
 - inductive output, **365ff**, 366g, 366s
 - input current, 274r, 307, 310, **332ff**, 332t, 333, 334
 - vs GBW, 310g
 - vs slew rate, 310g
 - input protection, 213, 215, 215s, **353ff**, 354
 - integrator, 272r
 - inverting amplifier, 272r
 - noise, 273r, 307, 310, 332t
 - vs quiescent current, 311g
 - noninverting amplifier, 272r
 - nonlinear circuits, 273r
 - offset voltage, 273r, 299, 332t
 - offset voltage drift, 273r
 - output current, 274r, 308
 - limiting, 351, **351ff**, 351s, 352
 - output impedance, 274r, 340g
 - output impedance vs frequency, **365ff**
 - output impedance vs frequency, 366g, 366s
 - output swing, 274r
 - peak detector, 273r
 - phase shift, 274r
 - PSRR, 324, 324g, **324ff**, 325, 325g
 - quiescent current, 307
 - rail-to-rail, 273, 274r, **336ff**
 - distortion, **339ff**, 340g
 - input crossover, 336g
- op-amp (cont.)
- output crossover, **339ff**, 340g
 - output impedance, 336
 - output linearity, **339ff**
 - output saturation, 294, **336ff**, 337g, 338s, 339
 - when isn't, **336ff**, 337g, 338s
 - resistorless gain stage, 346, **346**, 346s, 347g, 347s
 - sample-and-hold, 273r
 - settling time, 310, **342ff**, 342, 343s, 343t, 344s
 - vs f_T , 342
 - vs GBW, 311g
 - vs output step, 343, 343g
 - vs slew rate, 311g
 - single-supply, 273r
 - slew rate, 274r, 309, **328ff**, **342ff**, 342, 343s, 343t, 344s
 - Butler circuit, 329, 330
 - CFB, 330
 - cross-coupled input stage, 330
 - enhanced, **343**
 - increasing, 328
 - transconductance reduction, 329
 - vs f_T , 342
 - vs GBW, 310g, 328, 328, 329t
 - vs input error, 329g, 331g
 - vs quiescent current, 309g
 - SPIICE model, 279, 281
 - frequency response, 281g
 - step response, 282g
 - split feedback, 248
 - vacuum tube, 276, 276p
 - VFB+CFB, 319
 - voltage feedback, 304, **304ff**, 312–315T, 320
 - bandwidth, 318g
- optical
- conversion factors, 459
 - power, 459
 - power transmission, **461ff**, 462g, 462p, 464g, 464p
 - units, 459
- optocoupler
- for isolated feedback, 416, 428
- optoelectronics
- photodiode, 462g, 462p
 - photomultiplier
 - silicon, 448
 - photovoltaic stack, 461, 462, 464g, 464p
- oscillator, 273r, 393r
- blocking, 428
 - CMOS, 218
 - phase-shift, 434, 434
 - sinewave
 - Wien bridge, 39
 - trapezoidal, 435
 - triangle, 435
- oscilloscope
- overdrive artifacts, **343**, 344, 345s
 - probe
 - opto-fiber isolated, 462, 462p, 463
- Ott, H., 10n
- output
- decoupling, 378
- overtemperature
- shutdown, 428
- overvoltage
- shutdown, 395r
- parallel
- impedances, 3r
- paramagnetic, 50
- PCB
- capacitance, 7, 8g
 - inductance, 8g
 - maximum current, 7, 7g
 - meandering trace, 9
 - parasitic coupling, 12
 - traces, **6**
- PCB transmission line
- attenuation, 7
 - characteristic impedance, 7
 - geometries, 8
 - impedance, 8g, 9t
- peak detector
- eliminating diode leakage in, 364, 364
- peaking, 152
- vs phase margin, 280g

- Pease, Bob., 138
- permeability, 46, 50
effective, 55, 55, 56, 57g
- phase
margin, 371
- phase margin, **278ff**, 279g, **279**, 280g
- Philbrick, **276ff**
- photodiode
avalanche, 348, **348**, 349
biased, 284
- photometer
starlight-to-sunlight, **293ff**, 295, 295g
- photometric units, 459
- photomultiplier
silicon, **348ff**, 348p, 349, 349g, 350, 350s
- piezo
charge-dispensing driver, **266ff**, 267, 268
nonlinearity, 266g
- pole, 3r
dominant, 290
pair, 209
- pole-zero
network, 66, 66
- poles and zeros, **65ff**, 66
of Butterworth filter, 67
- potentiometer
digital, 28, 29, 30t
parameters, **28**
gang matching, 31
nonlinearity, 32
taper, 30
tempco, 32
volatility, 29
- power
entry module, 392r
factor
correction in offline SMPS, 392r, **418ff**, 418s, 419
in offline SMPS, 392r
linear, 418
in resistor, 23, 26g
on a beam of light, **461ff**, 462p, 464g, 464p
optical, **459**
spectrum, 433s, 435s
- power (cont.)
transient, **23**, 26g
transistor
mounting, 154
- power supply
Apple charger, 430p, 431
common-mode noise, 432, **432ff**, 433s, 435s, 435T, 436s
counterfeit, **428ff**, 429p, 429s, 430p, 431
crowbar, **412**, 413
current limit
foldback, 402, 402
efficient, 415, **415**
high-voltage
discharge circuit, 427, 427, 427s
laboratory, 453, **453ff**, 454, 455p, 457s
low-noise, 453, **453ff**, 454, 455p, 457s
negative, 448, 449
low-voltage, 400, **400**, 400s, 401
negative, 450, 450
noise, 457s
offline
non-isolated, 437, 437, 437s, 438, 438s, 439, 440
output impedance, 457
ripple voltage, 416, 428, 429s
safety, **428ff**
split, 442
splitter, 300, 301
stability, 457
switchmode
efficient, 415, **415**
ultra-isolated, 432, **432ff**, 434
unregulated, 392r, 455
- powerline
transients, 474g
- probe
active, 129, **213ff**
high impedance, **213ff**
high-voltage, **213ff**
'scope, 247
- protection
reverse polarity, 396, **396**
- PSACRF, 14t
- PSNEXT, 14t
- pulse
generator
bipolarity, 249, 250
fast, **150ff**, 151, 152, 153s
high-voltage, 88, 89s, 244, **244ff**, 246, 248, 248s, 249, 250, 330, 330s, 331
monitor, 247, 249
overcurrent limit, **423**, 424
overshoot, 153s
reversible, 247, 249
step response, 152, 153s
standard test, 475, **481**, 482g
- Purcell, E.M., 50n
- push-pull
BJT output stage, 100r, 256
MOSFET output stage, 256
- PWM, 392r
motor drive, **403ff**, 404, 404s
ripple reduction in, 383, **383**, 384s, 385
sensitivity, 385g
settling time, **383**, 384s
- radiometer, 461, 461p
- ramp
high-voltage, 262, 263
- Rayleigh, Lord., 48n
- RC circuit, 65
poles and zeros, 66
- rectifier
active, 273r
bridge, 392r
leakage, 78g
recovery spike, 410, 410, 411s, 430, 456
synchronous, 273r
- reference
design, 430
- relay, **68ff**, 69, 70p
ac coil, 74
advantages, 68
arcing, 69
coax, 71p
coil suppression, **71**, 72, 73s, 74, 74t
contact erosion, 72
contact protection, **69**

- relay (cont.)
 contactor, 265
 disadvantages, 68
 dry-switching, 68
 kickstart, 74, 75, 75s
 lifetime, 68
 mechanical, 69, 70p
 mercury-wetted, 69p
 overdriving, 74, 75, 75s
 parameters, 75
 reed, 69p, 76
 RF, 70p
 time-delay, 71p
 timing, 73s, 74, 74t, 75s
- resistance
 negative, 90, 406
 2-terminal, 146, 146, 146g, **146**, 147g
 sheet, 7
 temperature sensor (RTD), **468**, 470g
- resistor, 2r, **20ff**
 4-wire, *see also* resistor, Kelvin, **23**, 24, 25p
 Ayrton–Perry, 21
 current-sensing, 423
 dead, 28p
 departure from ideal, **20ff**
 digital, **28**, 29, 30t
 cautions, 32
 frequency response, 31g
 gang matching, 31
 log approximation, 31g
 parameters, **28**
 tempco, 32
 volatility, 29
 wiper resistance, 32, 32
- divider, **26**
 exploding, 477
 Kelvin, **23**, 24, 25p
 noise, 22
 nonlinearity, **21ff**, 23g, 32
 power
 derating, 24
 precision, 20, **26**
 self capacitance, **20**
 self inductance, **20**, 21, 22g
 tempco, 20, 468
 testing to failure, 24, 26, 27, 28p, 29s
- resistor (cont.)
 transient power, **23ff**, 26g
 voltage coefficient, **21ff**, 23g
 wirewound, 21, 22g
- RF
 choke, **59ff**, 61, 62g, 62p, 63g
 bank-winding, 62
 driving cable, 301, 301
- ripple, 392r
 PWM
 reduction, 383, **383**, 384s, 385, 385g
- root locus, 65n
 RTD, 90, **468**, 470g
 RTG, 472
- s-plane, **65ff**, 66, 209
 visualizing, 67
- safe operating area (SOA), 155g, 395r, 451, 451g
- saturation
 current vs voltage, 181
 of magnetic core, 53
 voltage vs current, 181
- Schmitt trigger, 99r, 273r
 SCR, 252, 353, 412
 second breakdown, 255, 395r
 Seebeck effect, 471, 471g
- sensor
 barometric pressure, 470
 humidity, 470
 temperature, **465ff**, 473T
 change-of-state, 465
 crickets, 465
 finger test, 465
 FLIR, **466ff**, 466–468p, 473T
 pyrometer, 467, 473T
 RTD, **468**, 470g, 473T
 semiconductor, 448
 silicon, 469, 470g, 473T
 thermal cutout, 466
 thermistor, **470**, 473T
 thermocouple, 471, **471**, 472g, 473T
- series
 impedances, 3r
- SETI, 350
 sewing machine, 403
 rheostat controller, 405p
- shielded enclosure, **13ff**, 16p
 attenuation, 16g
 test circuit, 17
- shielding, **13ff**
 electrostatic, 433
 magnetic, 14t, 17g
- signal
 amplitude, 2r
- sinewave
 from square wave, 218, 435, 436
- skin depth, 10, 11g, 11p, 12g, 14
- slew rate
 of current source, 382
 of high-voltage amplifier, 374
- smoke, 475, 476p
 SMU, 181, 183, 254
 snubber, 264, 410, 415, 430
 solenoid, 47
 air-core, 47
 ferrite core, 52g, **52**, 52p, 53g
 inductance of, 47
- source follower
 bandwidth, 208, 209, **209ff**, 210g, 211, 211g
 capacitive load, 209, **209ff**, 210g, 211, 211g
 gain, 388
 JFET
 output impedance, 172, 173
 transconductance of, 172, 173
 MOSFET, 213, 214, 215, 215s
 bootstrapped, 213, 215, 215s
 transimpedance gain, 211g
- SPICE
 amplifier analysis, **110ff**
 BJT bandwidth vs current, 142g
 BJT model, 112g, **142**
 MOSFET models, 186g, **187ff**, 189, **189ff**, 189n, 190, 191
 capacitances, 190
 circuit, 189
 op-amp model, 279, 281

- SPICE, op-amp model (cont.)
 frequency response, 281g
 step response, 282g
 problems with, 111, 121
 Spirito effect, 182, 182g, 255n
 square wave
 from sine, 218
 square-loop
 B-H curve, 51s
 SSR, 76
 STB (set-top box), 61
 step
 response, 279g
 step response
 vs phase margin, 280g
 stripline, 8
 summing junction, 272r
 switch
 analog, 76
 arcing, 69
 choices, 72
 contact protection, **69**
 dry-switching, 68
 high-side, 421, **421**, 422T
 lifetime, 68
 mechanical, **68ff**
 parameters, 75
 thermal cutout, 466
 switching
 loss, 233
 switchmode (SMPS), 392r
 boost, 393r, 442
 bridge converter, 393r
 buck, 393r, 442
 buck–boost, 393r
 burst mode, 416
 bus converter, **442**, 443, 444, 445p
 isolated, 445, 445
 continuous-conduction mode, 417
 Ćuk, 393r
 current pulsation, 444
 current-mode, 394r
 pros and cons, 394r
 efficiency, 415, **415**, 417g
 flyback, 393r, 428
 forward converter, 393r
 hysteretic, 394r
 inductor selection, 60
 switchmode (cont.)
 inductorless, 392r
 inverting, 393r
 isolated, 393r
 kickstart, 416
 multiphase, 444, 445p
 negative output, 446, **446**, 447
 PWM, 394r
 regulation, 394r
 ripple, 416
 SEPIC, 393r
 topologies, 393r
 voltage-mode, 394r
 temperature coefficient
 BJT leakage current, 102
 FET gate current, 102
 offset voltage, 273r
 temperature compensation
 bandgap reference, 394r
 Terman, F.E., 10n, 61n
 Thévenin equivalent Circuit, 3r
 Thévenin equivalent circuit, 3r
 thermal
 capacity, 482
 thermal emissivity, 467
 thermal resistance, 154, 394r
 pathetic, 198
 transient, **23**, 26g, 81g, 395r, 482g, **482**, 483g
 thermal scar, 467p
 thermistor, **470**
 thermocouple, 471, **471**, 472g
 thermoelectric cooler, 471
 thermometry, **465ff**
 thermopile, 472
 thyristor, 252
 toroid
 ferrite core, **52**
 train
 electric, 403
 rheostat controller, 406p
 transformer
 B-H curve, 51s
 dc, 442, **442**, 443, 444, 445p
 isolated, 445, 445
 in switchmode converter, 392r
 leakage inductance, 411t
 transformer (cont.)
 parasitics, 411t
 powerline, 392r
 toroidal, 456
 ultra-isolated, 433
 transient
 edge, 433
 power-on, 456
 protection, 475, 476p
 suppressor, 392r, **474ff**, 475, 475, 476p, 477, 478
 inductive circuit example, 479, 480
 non-sacrificial, 478
 series-mode, 478, 479
 test circuit, **480**, 481
 test pulses, 475, **481**, 482g
 thermal resistance, 185, 238, 238g, 240g, 395r, **474ff**, 482g, **482**, 483g
 transimpedance amplifier, 179, 272r
 and cascode, 108, 109
 autoranging linear, 296, **296**
 Bode plot, 284
 capacitive feedback, 326, **326**, 327s
 reset, 326
 compensation, 292
 current ratio, **360**, 361
 damping ratio, 284, 285t
 frequency response, 285g, 285t
 gain-switching, **289**, 290, 297, **297**
 noise filter, 288, 290
 response, 290g
 normalizing, **360**, 361
 photodiode, **288ff**, 289
 response, 289s
 PIN diode, **285**, 286
 speed, 286
 stability, **283ff**, 286
 stabilizing, 284, 285g
 starlight-to-sunlight, **293ff**, 295, 295g
 step response, 285g
 wide-range linear, **291ff**, 292, 292, 293g, 296, **296**, 297
 wideband, **296**, 297, **297**

- transistor
 - mounting, 154
 - pass, 392, 393r
 - perfect, 305
 - switch, 98r
- transmission line, *see also* cable
 - characteristic impedance, 17
 - PCB, *see also* PCB
 - reflection, 17
 - termination
 - back, 244
- triac, 252
- trimmer
 - capacitance, 43, 44, 247, 287, 296, 379, 436
 - compensation, 291, 379
 - gain, 346
 - offset, 191, 248, 277, 288, 332, 360, 362
 - pole-zero, 456
 - resistance, 28, 32, 33, 131, 152, 213, 214, 267
- TVS, 474, 475, **475**, **476**, 478
 - circuit example, 479, 480
 - for fast-switching magnet, 479, 480
 - test circuit, **480**, 481
 - vs MOV, 477
- undervoltage
 - lockout, 394r, 423
- varactor, 80, 81, 82g
- varistor, 353, 474, 475, **475**, 476p, 477, 478
- video
 - differential, 301
 - driver, 301, 301
- voltage, 2r
 - “let-through”, 474
 - arc, 475
 - divider, 26, 247
 - high-voltage, 378, 379
 - wideband, 378, 379
 - Early, 122, 122, 123g
 - formulas, 123
 - measuring, 122
 - firing, 475
 - holdover, 475
 - inverter
 - for RRO op-amp, 338, 339
 - protection, **474ff**
 - startup transient, 456
 - voltage reference, 393, 394r, 416, 456
 - bandgap, 394r
 - JFET pinchoff, 394r
 - MOSFET floating gate, 394r
 - noise, 394r, 456
 - series, 394r
 - tempco, 394r, 456
 - VI plot, 80g
 - zener, 394r
- voltage regulator
 - 3-terminal, 393r
 - 317-style, 193, 393r
 - current limit
 - foldback, 402, 402
 - dropout, 393r
 - in current source, 193
 - linear, 392, 393r
 - low-dropout, 393r
 - low-dropout (LDO)
 - stability, 393r
 - taxonomy, 392r
- wave
 - ring, 481
- Wheeler, H.A., 48, 61n
- Widlar, Bob
 - transconductance configuration, 380, 380
- Wien, M., 48n
- wire, **5ff**, 6t
 - current in, 5, 5g
 - gauge, 5
 - inductance of, 10, 10g
 - insulation, **5ff**
 - Kynar, 5
 - litz, 5, 12
 - magnet, 5
 - resistance, 5
 - solid, 5
 - stranded, 5, **5**
 - Teflon, 5
 - tinned, 6
- zener
 - BJT as, 194n
 - capacitance, 81, 82g, 83, 478
 - low-capacitance, 377
- zero-voltage switching, 429, 430